



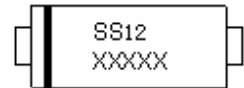
SS12 THRU SS110 SCHOTTKY RECTIFIER

Features:

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low Power Loss, High Efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed:250 C/10 seconds at terminals
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data:

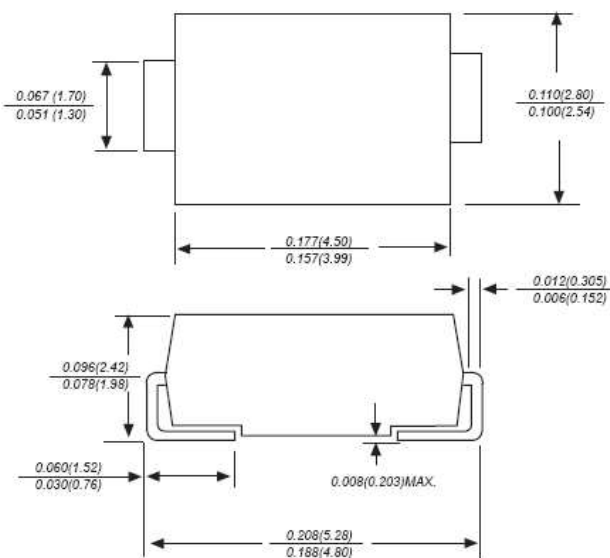
- Case: JEDEC SMA molded plastic body
- Terminals: leads solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Weight: 0.003 ounce, 0.093 grams
- Mounting Position: Any



SS12

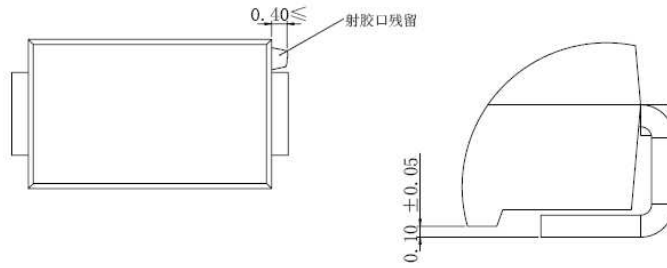
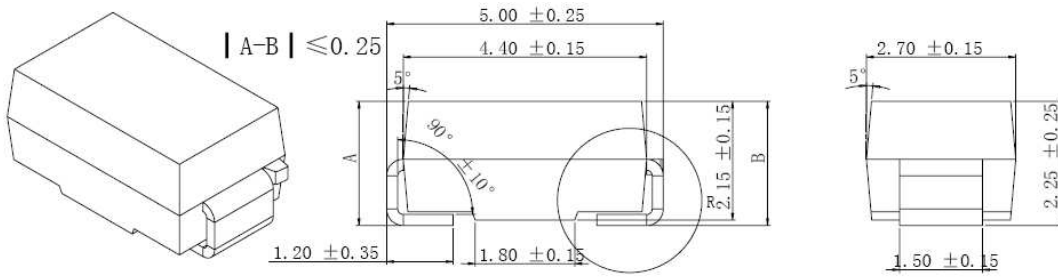
Mechanical Dimensions (In mm / Inches)

DO-214AC/SMA

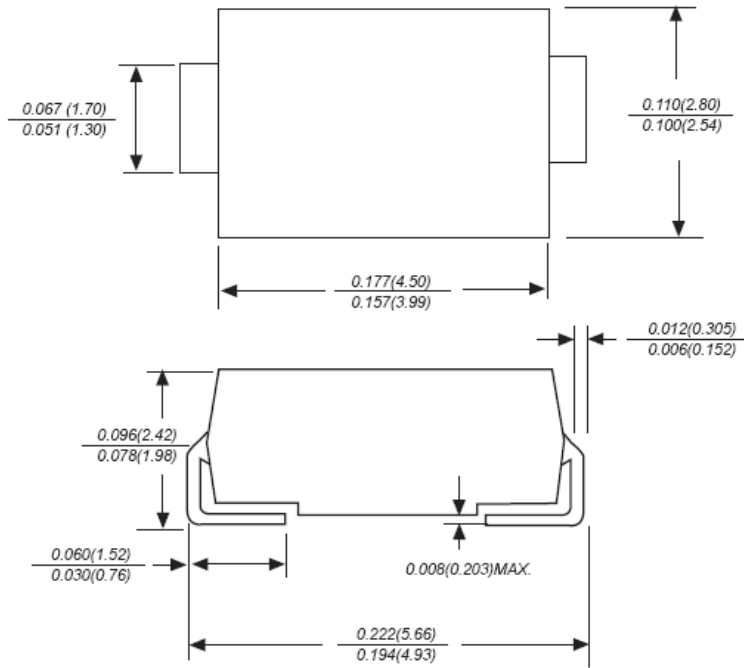


Dimensions in inches and (millimeters)

OPTION 1(XH)



OPTION 2(JK)



OPTION3(XH Da Bian)

SMA

MARKING, MOLDING RESIN

Marking for SS12/13/14/15/16/18/110, 1st row SS12/13/14/15/16/18/110, 2nd row YYWWL

Where YY is the manufacture year

WW is the manufacture week code

L is the wafer's Lot Number



Ordering Information:

Device	Package	Shipping
SS12 THRU SS110	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics

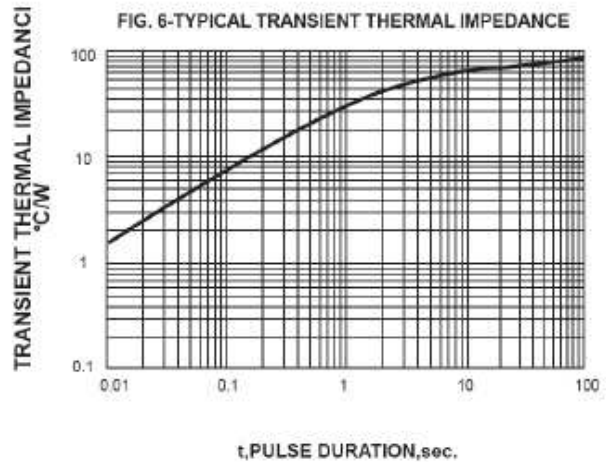
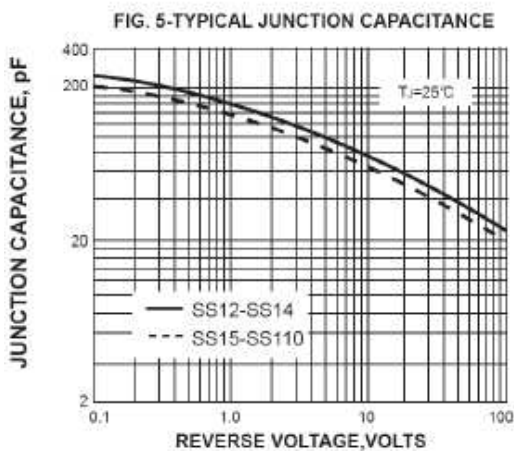
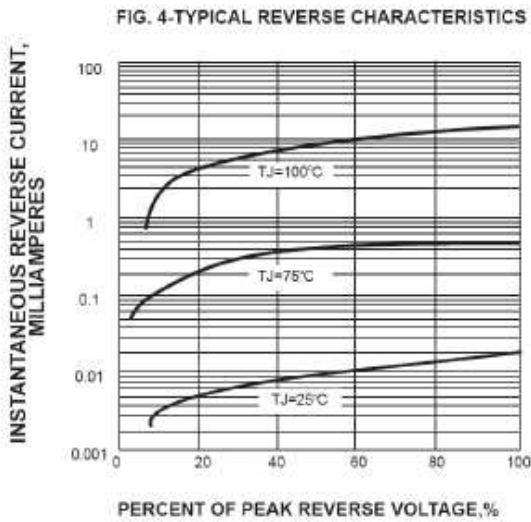
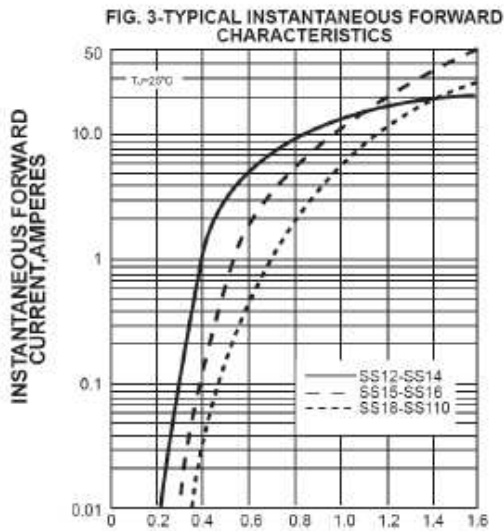
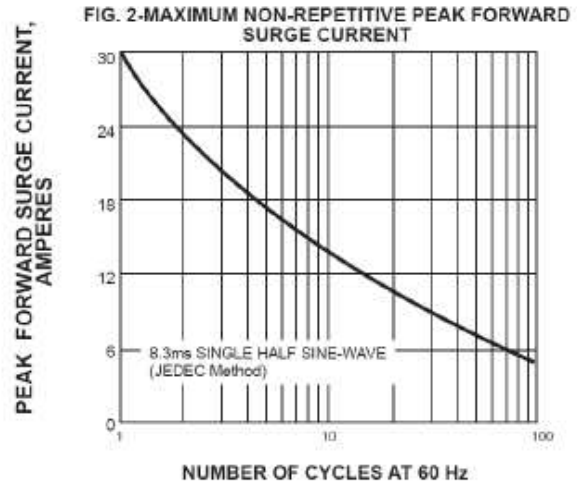
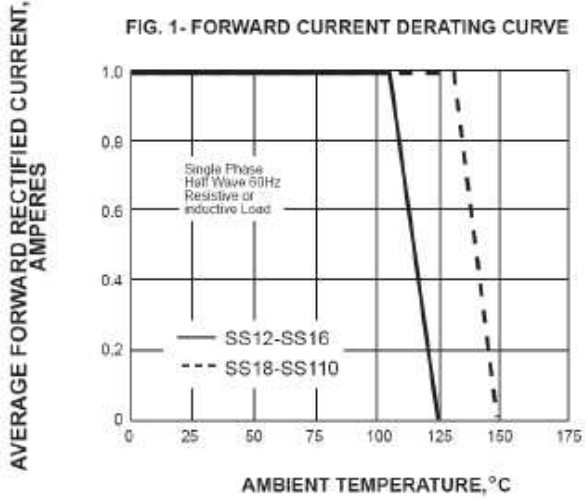
Ratings *at 25 C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	SS12	SS13	SS14	SS15	SS16	SS18	SS110	UNITS	
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	VOLTS	
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	VOLTS	
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	VOLTS	
Maximum average forward rectified current at T_L (see fig.1)	$I_{(AV)}$	1.0							Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0							Amps	
Maximum instantaneous forward voltage at 1.0A	V_F	0.45	0.55	0.70		0.85			Volts	
Maximum DC reverse current at rated DC blocking voltage $T_A=25\text{ C}$ $T_A=100\text{ C}$	I_R	0.5							mA	
		10.0					5.0			
Typical junction capacitance (NOTE 1)	C_J	110			90				pF	
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	88.0							C/W	
Operating junction temperature range	T_J	-65 to +125					-65 to +150			C
Storage temperature range	T_{STG}	-65 to +150							C	

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas





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